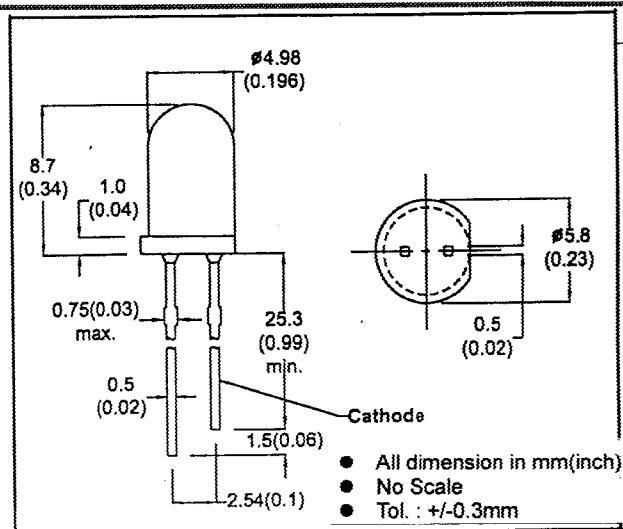


DESCRIPTION

MIB51T is GaAlAs infrared emitting diode molded in T-1 3/4 standard 5mm diameter clear transparent lens.



ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	160mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

* Pulse Width = 10μs, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	P _o		4.0		mW	IF=20mA
Forward Voltage	V _F			1.6	V	IF=20mA
Reverse Current	I _R			100	μA	V _R =5V
Half Intensity Beam Angle	θ _{HI}		70		degree	IF=20mA
Peak Wavelength	λ _p		940		nm	IF=20mA
Spectrum Line Half Width	Δλ		45		nm	IF=20mA



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MIB51T

